

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1366	349/139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:49
L2	1378	257/79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03
L3	10	257/E51.005	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03
L4	2	257/E33.064	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03
L5	0	257/E31.126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03
L6	8	257/E29.151	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:04
L7	0	257/E23.157	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:04
L8	5037	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:29

L9	185	257/449	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:31
L10	191	257/749	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:34
L11	4116	257/347	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:34
S1	640	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide)	USPAT	OR	ON	2005/03/31 19:21
S2	45	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide) near electrode and (ITO or indium near tin near oxide) near (layer or film or structure)	USPAT	OR	ON	2005/03/31 19:36
S3	0	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide) near gate and (ITO or indium near tin near oxide) near (source or drain)	USPAT	OR	ON	2005/03/31 19:37
S4	0	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) near gate near electrode and (ITO or indium near tin near oxide) near (source or drain)	USPAT	OR	ON	2005/03/31 19:37
S5	82	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16

S6	281	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) same gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S7	259	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S8	259	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S9	278	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/04/01 13:43
S10	177	S8 not S5	USPAT; JPO	OR	ON	2005/03/31 20:17
S11	94	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/03/31 20:54
S12	12	S11 not S5	USPAT; JPO	OR	ON	2005/03/31 20:55
S13	2	257/79 and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/04/01 13:44
S14	6	257/79 and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) same gate near electrode same (source or drain)	USPAT; JPO	OR	ON	2005/04/01 14:29

S15	1215	349/139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:48
S16	899	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:28
S17	528	349/152	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:37
S18	7213	(ITO or indium near tin near oxide) with (residue or remnant or left near over or ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
S19	10	(ITO or indium near tin near oxide) with (residue or remnant or left near over) with (ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:42
S20	6749	(ITO or indium near tin near oxide) with (ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:47
S21	3375	(ITO or indium near tin near oxide) with (ring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:43
S22	221	(ITO or indium near tin near oxide) with (ring) with (wir\$3 or film or layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:44

S23	212	(ITO or indium near tin near oxide) with (ring) with (enclosure\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
S24	3608	(ITO or indium near tin near oxide) with (enclosure\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
S25	2	(ITO or indium near tin near oxide) with (residue or remnant or left near over) with (enclosure\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:05
S26	4646	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:15
S27	174	257/449	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:28
S28	172	257/749	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:37
S29	5	257/e51.005	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:44
S30	1214	257/79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:56

S31	3773	257/347	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:08
S32	1825	257/350	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:18
S33	269	257/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:33
S34	1	257/E33.064	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
S35	0	257/E31.126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
S36	4	257/E29.151	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
S37	0	257/E23.157	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:35
S38	132	438/609	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:36

S39	2549	174/255	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:37
S40	1044	174/256	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:45
S41	807	174/257	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 18:02
S42	938	174/258	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 18:02